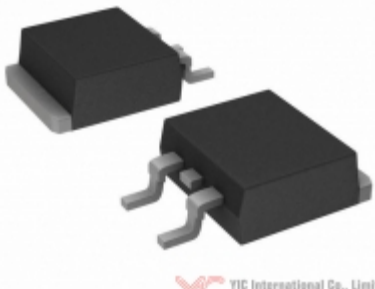











	<h2 style="color: red;">IRFBE30STRLPBF</h2>	
	Hersteller-Teilenummer:	IRFBE30STRLPBF
	Hersteller / Marke:	Electro-Films (EFI) / Vishay
	Teil der Beschreibung:	MOSFET N-CH 800V 4.1A D2PAK
Datenblätter:	 IRFBE30STRLPBF.pdf	
RoHs Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 9171 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	IRFBE30STRLPBF
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 800V 4.1A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	9171 pcs Stock
Hersteller Standard Vorlaufzeit	18 Weeks
detaillierte Beschreibung	N-Channel 800V 4.1A (Tc) 125W (Tc) Surface Mount
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D2PAK
Verlustleistung (max)	125W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (V _{dss})	800V
Strom - Ununterbrochener Abfluss (I _d) bei 25 ° C	4.1A (Tc)
R _{ds} On (Max) @ I _d , V _{gs}	3 Ohm @ 2.5A, 10V
V _{GS} (th) (Max) @ I _d	4V @ 250µA
Gate Charge (Q _g) (Max) @ V _{gs}	78nC @ 10V
Eingabekapazität (C _{iss}) (Max) @ V _{ds}	1300pF @ 25V
Antriebsspannung (Max R _{ds} On, Min R _{ds} On)	10V
V _{gs} (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)


IRFBE30STRLPBF ist neu im Original, Suche IRFBE30STRLPBF Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie IRFBE30STRLPBF Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage IRFBE30STRLPBF: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>IRFBE30STRR Vishay / Siliconix MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30STRLPBF Vishay / Siliconix MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30SPBF Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE20 Electro-Films (EFI) / Vishay MOSFET N-CH 900V 1.7A TO-220AB</p>
 <p>IRFBE30SPBF Vishay / Siliconix MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30S Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30STRR Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30STRL Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A D2PAK</p>

heiße Teile

Mehr

 IRFBC40LCPBF	 IRFBC40LCPBF	 IRFBC40LPBF	 IRFBC40LPBF	 IRFBC40S
 IRFBC40S	 IRFBC40SPBF	 IRFBC40SPBF	 IRFBC40STRL	 IRFBC40STRL
 IRFBC40STRLPBF	 IRFBC40STRLPBF	 IRFBC40STRR	 IRFBC40STRR	 IRFBC41LC
 IRFBE20PBF	 IRFBE20PBF	 IRFBE20SPBF	 IRFBE30L	 IRFBE30L
 IRFBE30LPBF-M	 IRFBE30PBF	 IRFBE30PBF	 IRFBE30SPBF	 IRFBE30SPBF
 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF	 IRFBE30SPBF	 IRFBE30SPBF
 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF	 IRFBE30SPBF	 IRFBE30SPBF
 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF	 IRFBE30SPBF	 IRFBE30SPBF
 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF	 IRFBE30SPBF	 IRFBE30SPBF
 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF	 IRFBE30SPBF	 IRFBE30SPBF

Contact us:Info@Y-IC.com

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